



UT6898

Power MOSFET

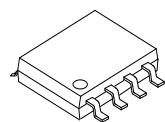
N-CHANNEL ENHANCEMENT

■ DESCRIPTION

The **UT6898** uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

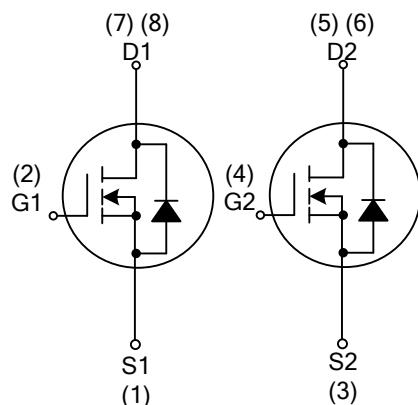
■ FEATURES

- * $R_{DS(ON)} \leq 14 \text{ m}\Omega @ V_{GS}=4.5\text{V}, I_D=9.4\text{A}$
- * $R_{DS(ON)} \leq 18 \text{ m}\Omega @ V_{GS}=2.5\text{V}, I_D=8.3\text{A}$
- * Low capacitance
- * Low gate charge
- * Fast switching capability
- * Avalanche energy specified



SOP-8

■ SYMBOL



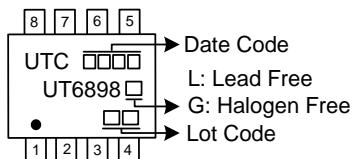
■ ORDERING INFORMATION

| Ordering Number | | Package | Pin Assignment | | | | | | | | Packing |
|-----------------|---------------|---------|----------------|---|---|---|---|---|---|---|-----------|
| Lead Free | Halogen Free | | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | |
| UT6898L-S08-R | UT6898G-S08-R | SOP-8 | S | G | S | G | D | D | D | D | Tape Reel |

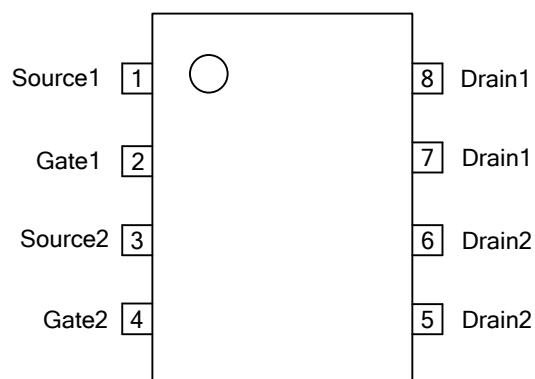
Note: Pin Assignment: G: Gate D: Drain S: Source

| | | |
|---------------|--|---|
| UT6898G-S08-R | (1)Packing Type (2)Package Type (3)Green Package | (1) R: Tape Reel (2) S08: SOP-8 (3) G: Halogen Free and Lead Free, L: Lead Free |
|---------------|--|---|

■ MARKING



■ PIN CONFIGURATION



■ ABSOLUTE MAXIMUM RATING ($T_C=25^\circ\text{C}$, unless otherwise specified)

| PARAMETER | SYMBOL | RATINGS | UNIT |
|--|----------------|------------|------------------|
| Drain-Source Voltage | V_{DSS} | 20 | V |
| Gate-Source Voltage | V_{GSS} | ± 12 | V |
| Continuous Drain Current | I_D | 9.4 | A |
| Pulsed Drain Current | I_{DM} | 38 | A |
| Maximum Power Dissipation | P_D | 3.1 (Note) | W |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 ~ +150 | $^\circ\text{C}$ |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ THERMAL DATA

| PARAMETER | SYMBOL | RATINGS | UNIT |
|------------------|---------------|---------|--------------------|
| Junction-to-Case | θ_{JC} | 40 | $^\circ\text{C/W}$ |

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

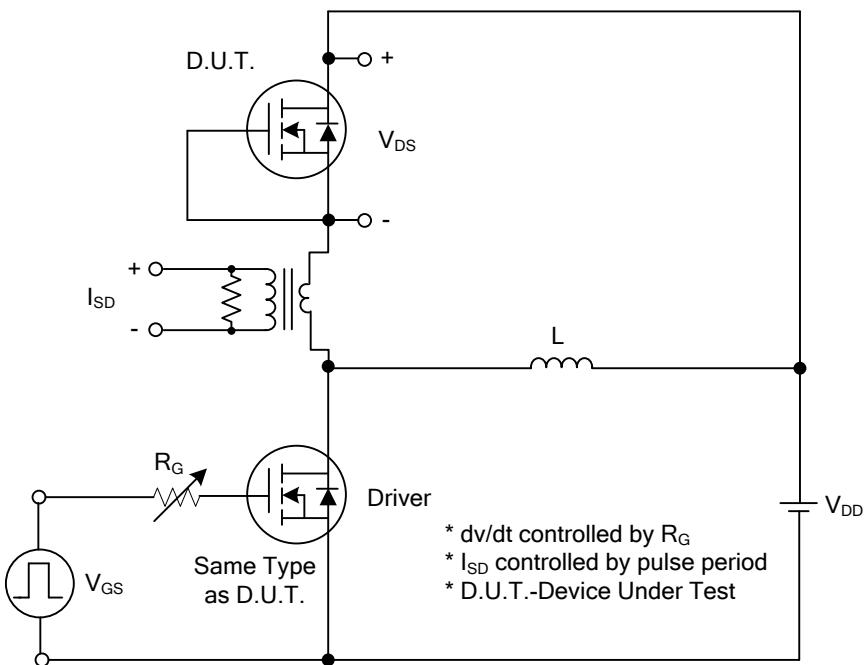
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|--------------|--|-----|------|-----------|------------------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0\text{V}, I_D=250\mu\text{A}$ | 20 | | | V |
| Drain-Source Leakage Current | I_{DSS} | $V_{GS}=0\text{V}, V_{DS}=16\text{V}$ | | | 1 | μA |
| Gate-Source Leakage Current | I_{GSS} | $V_{GS}=\pm 12\text{V}, V_{DS}=0\text{V},$ | | | ± 100 | nA |
| ON CHARACTERISTICS (Note 1) | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{DS}=V_{GS}, I_D=250\mu\text{A}$ | 0.5 | 1 | 1.5 | V |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}=4.5\text{V}, I_D=9.4\text{A}$ $V_{GS}=2.5\text{V}, I_D=8.3\text{A}$ | | 10 | 14 | $\text{m}\Omega$ |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Input Capacitance | C_{ISS} | $V_{GS}=0\text{V}, V_{DS}=10\text{V}, f=1\text{MHz}$ | | 2100 | | pF |
| Output Capacitance | C_{OSS} | | | 530 | | pF |
| Reverse Transfer Capacitance | C_{RSS} | | | 450 | | pF |
| SWITCHING PARAMETERS (Note 1) | | | | | | |
| Total Gate Charge | Q_G | $V_{GS}=10\text{V}, V_{DS}=10\text{V}, I_D=9.4\text{A}$ | | 48 | | nC |
| Gate Source Charge | Q_{GS} | | | 6.7 | | nC |
| Gate Drain Charge | Q_{GD} | | | 1.6 | | nC |
| Turn-ON Delay Time | $t_{D(ON)}$ | $V_{GS}=10\text{V}, V_{DS}=10\text{V}, I_D=9.4\text{A}$ $R_G=6\Omega$ | | 7 | | ns |
| Turn-ON Rise Time | t_R | | | 18 | | ns |
| Turn-OFF Delay Time | $t_{D(OFF)}$ | | | 52 | | ns |
| Turn-OFF Fall-Time | t_F | | | 24 | | ns |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS | | | | | | |
| Maximum Body-Diode Continuous Current | I_S | | | | 2.6 | A |
| Drain-Source Diode Forward Voltage | V_{SD} | $V_{GS}=0\text{V}, I_S=9.4\text{A}$ (Note 1) | | | 1.2 | V |

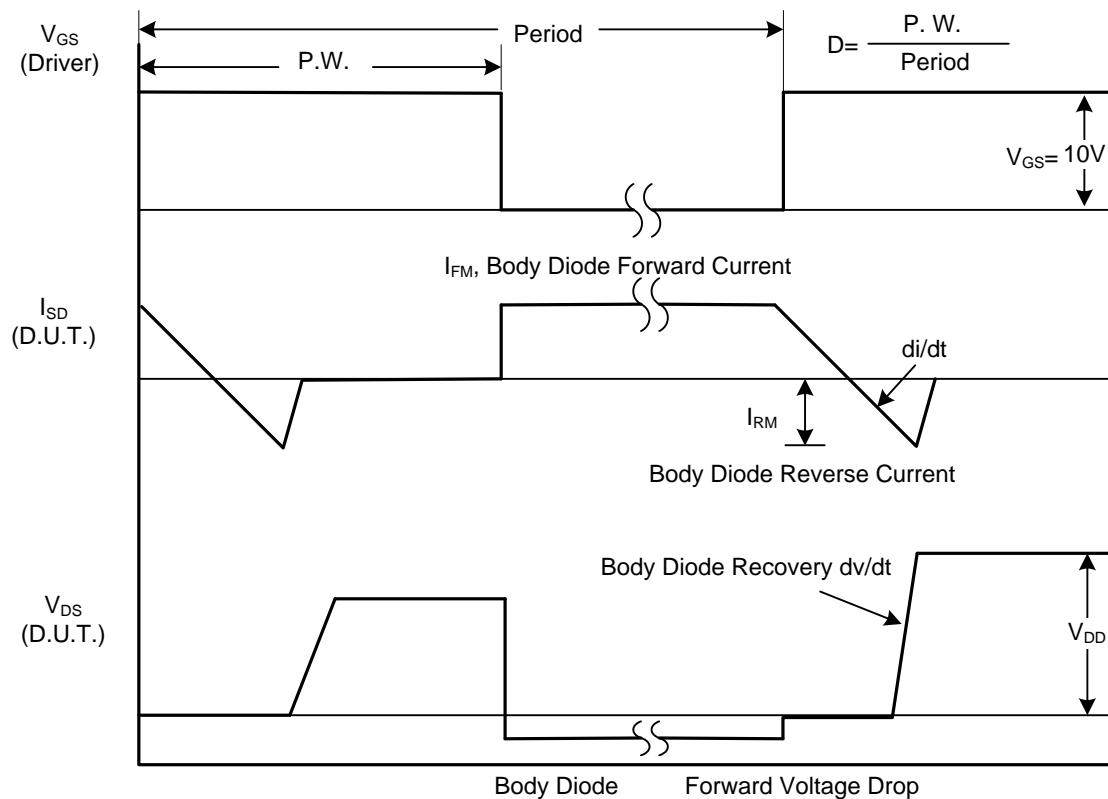
Notes: 1. Pulse Test: Pulse Width < 300ms, Duty Cycle < 2.0%

2. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied

■ TEST CIRCUITS AND WAVEFORMS

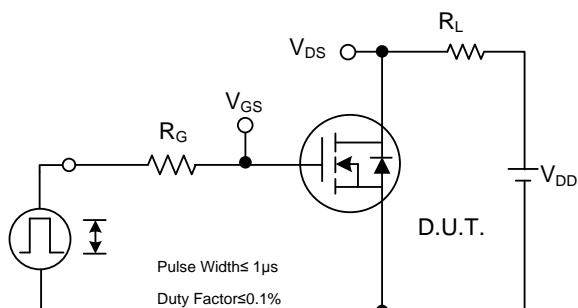


Peak Diode Recovery dv/dt Test Circuit

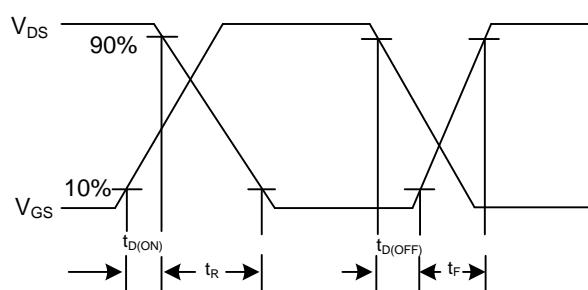


Peak Diode Recovery dv/dt Waveforms

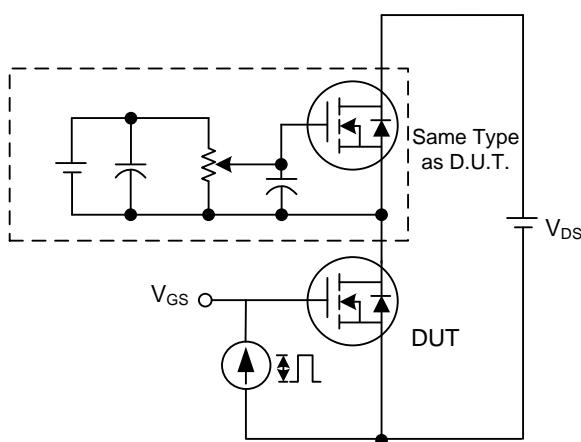
■ TEST CIRCUITS AND WAVEFORMS



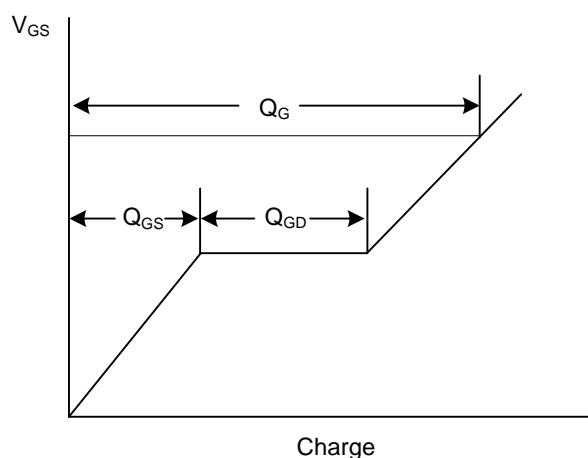
Switching Test Circuit



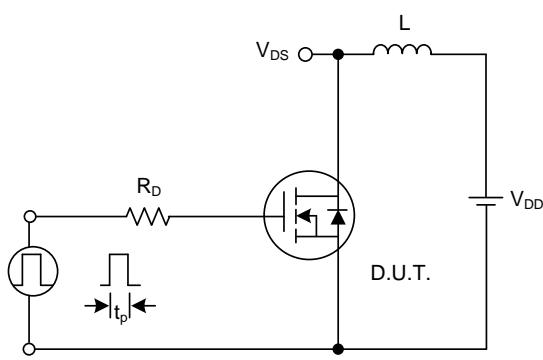
Switching Waveforms



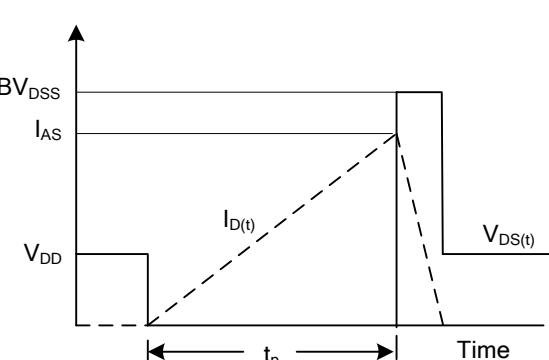
Gate Charge Test Circuit



Gate Charge Waveform

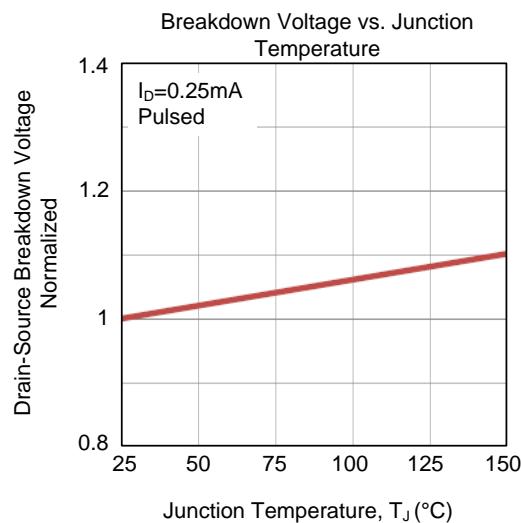
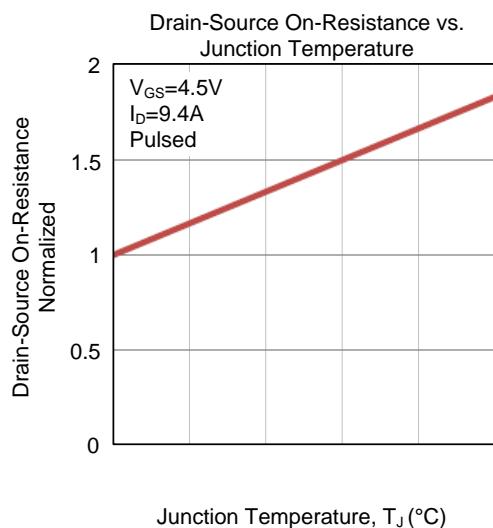
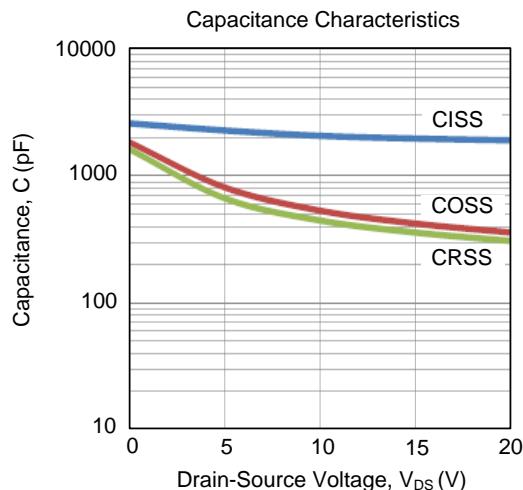
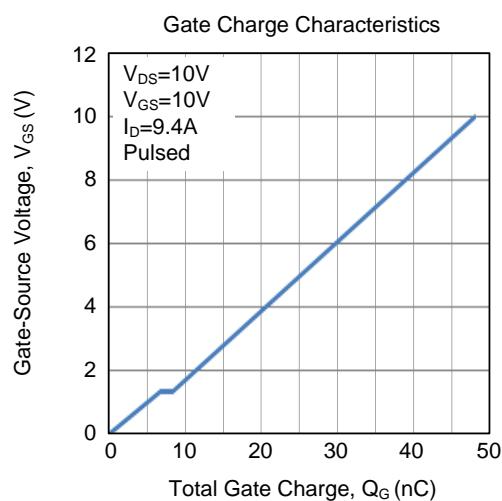
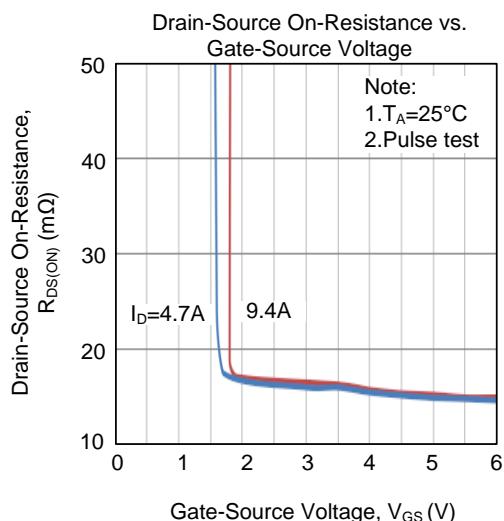
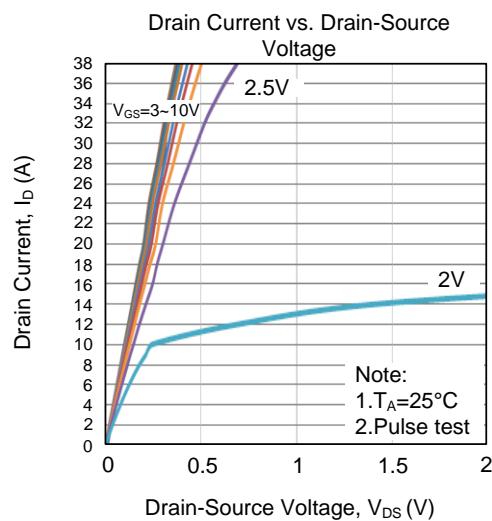


Unclamped Inductive Switching Test Circuit

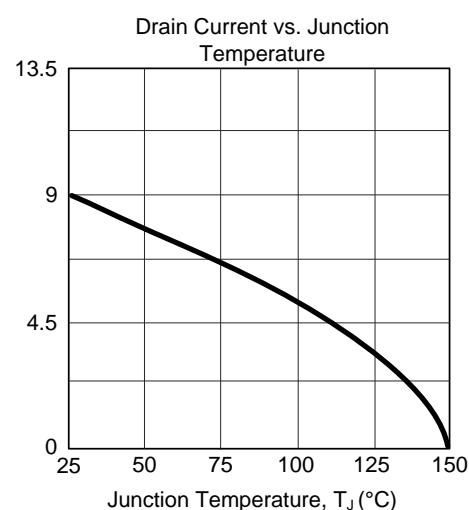
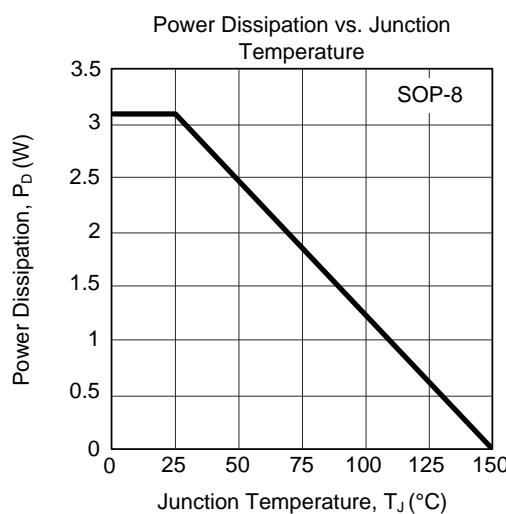
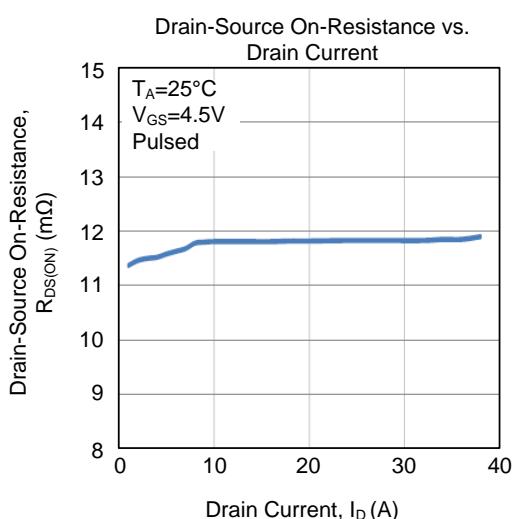
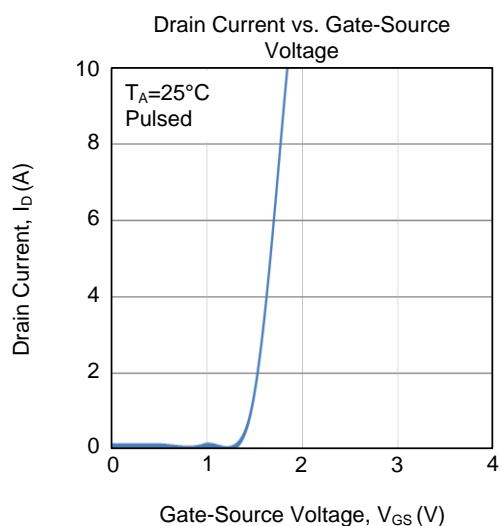
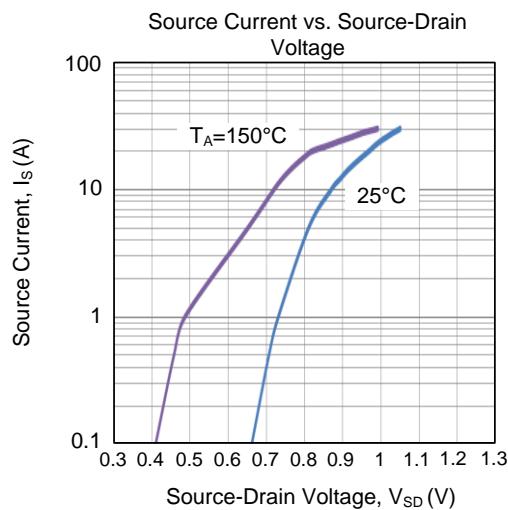
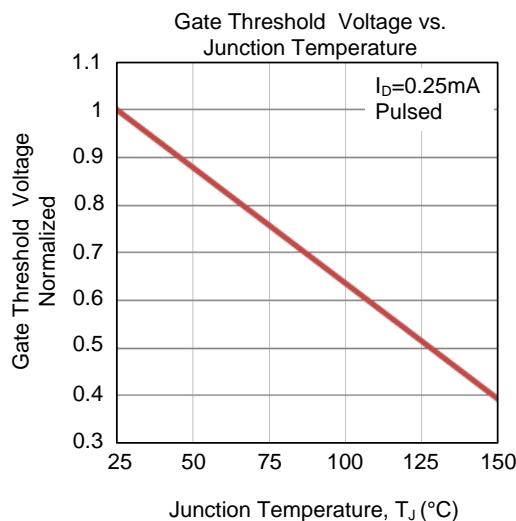


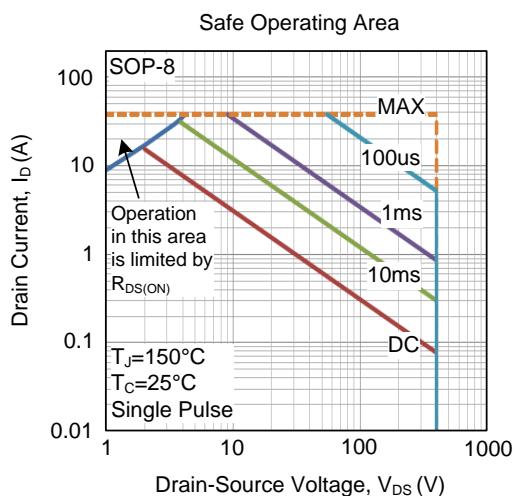
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)

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